

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	9	(((((single near3 event near3 upset) SEU) near5 (resist\$3 impeded\$3))) and (resist\$3 adj transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/07 15:58
L2	20	(((((single near3 event near3 upset) SEU) near5 (resist\$3 impeded\$3))) and (transistor near3 resistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/07 15:58
L3	34	((single near3 event near3 upset) SEU) and ((var\$5 program\$5 adjust\$4) near3 (impedance resistance))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/07 15:58
L4	67	(((((single near3 event near3 upset) SEU)) and ohm	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/07 15:58
L5	54	((single near3 event near3 upset) or SEU) and ((resist\$4 impeded\$5) near2 value)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/07 15:58
L6	30	((control\$5 program\$5 adjust\$4 variable) with transistor with (resist\$4 impeded\$4)) and ((single near3 event near3 upset) or SEU)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/07 15:58
L7	14	(((((single near3 event near3 upset) SEU) near5 (resist\$3 impeded\$3))) and ((resist\$3 impeded\$3) near2 value)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/07 15:59
L8	3	(((((single near3 event near3 upset) SEU) near5 (resist\$3 impeded\$3))) and (program\$5 near4 transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/07 15:59
L9	0	(((((single near3 event near3 upset) SEU) near5 (resist\$3 impeded\$3))) and (program\$5 near4 (resist\$3 impeded\$3))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/07 15:59

L10	2	(((single near3 event near3 upset) SEU) near5 (resist\$3 impeded\$3))) and (program\$5 with transistor with (resist\$3 impeded\$3))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/07 15:59
L11	3	(((single near3 event near3 upset) SEU) near5 (resist\$3 impeded\$3))) and (program\$5 near4 transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/07 15:59
L12	0	((((single near3 event near3 upset) SEU) near3 (resist\$3 impeded\$3))) and memory) and (sram)) and (program\$5 near4 (resist\$3 impeded\$3))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/07 15:59
L13	65	(((single near3 event near3 upset) SEU) near3 (resist\$3 impeded\$3))) and memory	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/07 15:59
L14	42	((((single near3 event near3 upset) SEU) near3 (resist\$3 impeded\$3))) and memory) and (sram)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/07 15:59
L15	85	(((single near3 event near3 upset) SEU) near3 (resist\$3 impeded\$3))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/07 15:59
L16	22	US-4956814-\$.DID. OR US-5126279-\$.DID. OR US-5301146-\$.DID. OR US-5307142-\$.DID. OR US-5311070-\$.DID. OR US-5889431-\$.DID. OR US-6058041-\$.DID. OR US-6172907-\$.DID. OR US-6180984-\$.DID. OR US-6271568-\$.DID. OR US-6278287-\$.DID.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/07 16:09
L17	24	US-4725875-\$.DID. OR US-4852060-\$.DID. OR US-4884238-\$.DID. OR US-4903094-\$.DID. OR US-5018102-\$.DID. OR US-5189598-\$.DID. OR US-5212108-\$.DID. OR US-5631863-\$.DID. OR US-6111780-\$.DID. OR US-6252433-\$.DID. OR US-6278287-\$.DID. OR US-6369630-\$.DID.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/07 16:09

L18	44	L16 or L17	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/07 16:09
L19	23	(US-20020109230-\$).did. or (US-4725875-\$ or US-4884238-\$ or US-4903094-\$ or US-4956814-\$ or US-5018102-\$ or US-5126279-\$ or US-5189598-\$ or US-5212108-\$ or US-5301146-\$ or US-5307142-\$ or US-5311070-\$ or US-5631863-\$ or US-5889431-\$ or US-6058041-\$ or US-6111780-\$ or US-6172907-\$ or US-6180984-\$ or US-6252433-\$ or US-6271568-\$ or US-6369630-\$).did. or (DE-3871945-\$ or US-6278287-\$). did.	US-PGPUB; USPAT; DERWENT	OR	OFF	2005/02/07 16:09
L20	1	L19 not L18	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/07 16:10
S1	25	((control\$5 program\$5 adjust\$4 variable) with transistor with (resist\$4 imped\$4)) and ((single near3 event near3 upset) or SEU)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/15 20:34
S2	51	((single near3 event near3 upset) or SEU) and ((resist\$4 imped\$5) near2 value)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/15 20:34
S3	61	((single near3 event near3 upset) SEU)) and ohm	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/15 20:34
S4	30	((single near3 event near3 upset) SEU) and ((var\$5 program\$5 adjust\$4) near3 (impedance resistance))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/15 20:34
S5	19	((single near3 event near3 upset) SEU) near5 (resist\$3 imped\$3))) and (transistor near3 resistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/15 20:34

S6	6	(((((single near3 event near3 upset) SEU) near5 (resist\$3 impeded\$3))) and (resist\$3 adj transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/15 20:34
S7	70	(((((single near3 event near3 upset) SEU) near3 (resist\$3 impeded\$3)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/07/31 19:01
S8	53	(((((single near3 event near3 upset) SEU) near3 (resist\$3 impeded\$3))) and memory	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/07/31 18:51
S9	33	(((((single near3 event near3 upset) SEU) near3 (resist\$3 impeded\$3))) and memory) and (sram)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/07/31 18:52
S10	0	((((((single near3 event near3 upset) SEU) near3 (resist\$3 impeded\$3))) and memory) and (sram)) and (program\$5 near4 (resist\$3 impeded\$3))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/07/31 18:52
S11	73	(((((single near3 event near3 upset) SEU) near5 (resist\$3 impeded\$3)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/08/01 18:48
S12	12	(((((single near3 event near3 upset) SEU) near5 (resist\$3 impeded\$3))) and ((resist\$3 impeded\$3) near2 value)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/07/31 19:06
S13	0	(((((single near3 event near3 upset) SEU) near5 (resist\$3 impeded\$3))) and (program\$5 with transistor with (resist\$3 impeded\$3))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/07/31 19:08
S14	0	(((((single near3 event near3 upset) SEU) near5 (resist\$3 impeded\$3))) and (program\$5 near4 (resist\$3 impeded\$3))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/07/31 19:08
S15	0	(((((single near3 event near3 upset) SEU) near5 (resist\$3 impeded\$3))) and (program\$5 near4 transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/07/31 19:35

S16	48814	resist\$3 near2 transistor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/07/31 19:35
S17	76238	transistor near3 resistor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/07/31 19:50
S18	59077	(control\$5 program\$5 adjust\$4 variable) with transistor with (resist\$4 imped\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/08/01 18:48
S19	18885	(control\$5 program\$5 adjust\$4 variable) near4 transistor near4 (resist\$4 imped\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/08/01 18:48
S20	838	(single near3 event near3 upset) or SEU	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/08/01 18:49
S21	841	((single near3 event near3 upset) SEU)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/08/18 18:11
S22	143	((((single near3 event near3 upset) SEU)) and memory and (resist\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/08/18 14:03
S23	21	(US-6369630-\$ or US-6271568-\$ or US-6180984-\$ or US-6058041-\$ or US-5311070-\$ or US-5307142-\$ or US-5212108-\$ or US-5189598-\$ or US-4956814-\$ or US-6252433-\$ or US-6172907-\$ or US-5889431-\$ or US-5301146-\$ or US-5018102-\$ or US-4884238-\$ or US-6111780-\$ or US-5631863-\$ or US-4903094-\$).did. or (US-20020109230-\$).did. or (US-6278287-\$ or DE-3871945-\$). did.	US-PGPUB; USPAT; DERWENT	OR	OFF	2003/08/18 15:36

S24	7	((US-6369630-\$ or US-6271568-\$ or US-6180984-\$ or US-6058041-\$ or US-5311070-\$ or US-5307142-\$ or US-5212108-\$ or US-5189598-\$ or US-4956814-\$ or US-6252433-\$ or US-6172907-\$ or US-5889431-\$ or US-5301146-\$ or US-5018102-\$ or US-4884238-\$ or US-6111780-\$ or US-5631863-\$ or US-4903094-\$).did. or (US-20020109230-\$).did. or (US-6278287-\$ or DE-3871945-\$). did.) and ohm	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/08/18 15:40
S25	0	10/125,666	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/12/17 19:51
S26	6400	resist\$3 adj transistor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/05/20 17:39
S27	1	10/125,666	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/07 13:43